

Room-Temperature Synthesis of Ultrasmall Sulfur-Free SnO<sub>2</sub> Quantum Dots as an Electron Transport Layer in Perovskite Solar Cells  
Supplementary material

Gidey, Abraha Tadese; Rad, Elnaz Ghahremani; Latosinsky, Katherine; SURESH, Sunil & Uhl, Alexander R. (2026) Room-Temperature Synthesis of Ultrasmall Sulfur-Free SnO<sub>2</sub> Quantum Dots as an Electron Transport Layer in Perovskite Solar Cells. In: Chemistry of Materials,.

DOI: 10.1021/acs.chemmater.6c01064

Handle: <http://hdl.handle.net/1942/49533>

## Supplementary Information

### Room-Temperature Synthesis of Ultra-Small Sulfur-Free SnO<sub>2</sub> Quantum Dots as Electron Transport Layer in Perovskite Solar Cells

Abraha Tadesse Gidey,<sup>1\*</sup> Elnaz Ghahremani Rad,<sup>1</sup> Katherine Latosinsky,<sup>1</sup> Sunil Suresh,<sup>1,2,3,4</sup>, and Alexander R. Uhl<sup>1\*</sup>

<sup>1</sup>Laboratory for Solar Energy and Fuels (LSEF), School of Engineering, The University of British Columbia, Kelowna V1V 1V7, Canada

<sup>2</sup>Now at: imec, IUMAT, Thor Park 8320, B-3600 Genk, Belgium

<sup>3</sup>Now at: UHasselt, Institute for Materials Research (IUMAT), Martelarenlaan 42, B-3500 Hasselt, Belgium

<sup>4</sup>Now at: EnergyVille, IUMAT, Thor Park 8320, B-3600 Genk, Belgium

\*Corresponding authors: [abraha.gidey@ubc.ca](mailto:abraha.gidey@ubc.ca) (A.T.G.) and [alexander.uhl@ubc.ca](mailto:alexander.uhl@ubc.ca) (A.R.U.)

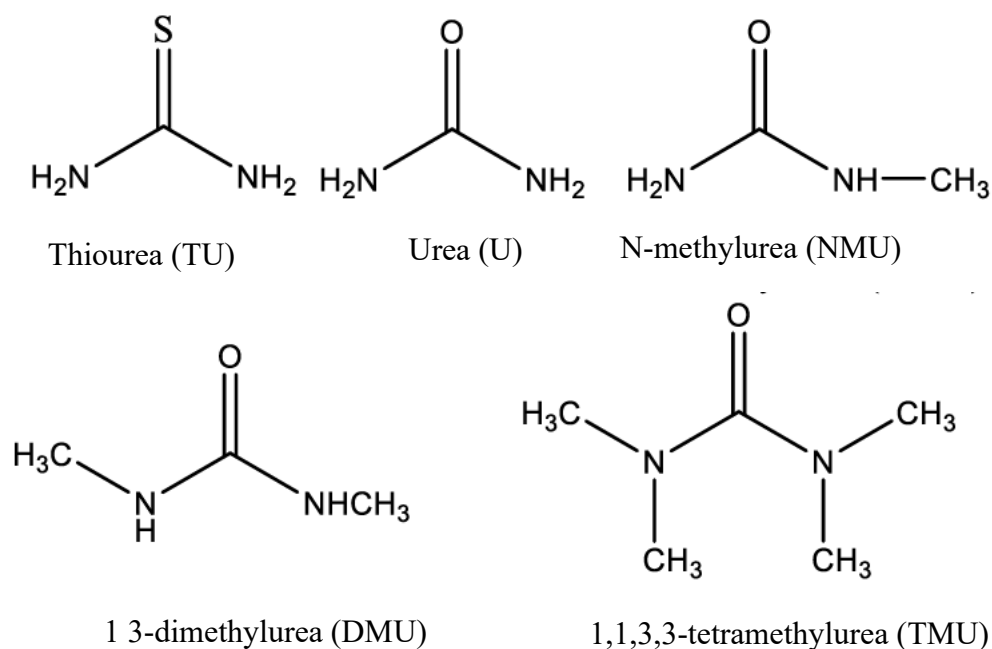


Figure S1. Chemical structures of the ligands used to synthesize SnO<sub>2</sub> QDs.

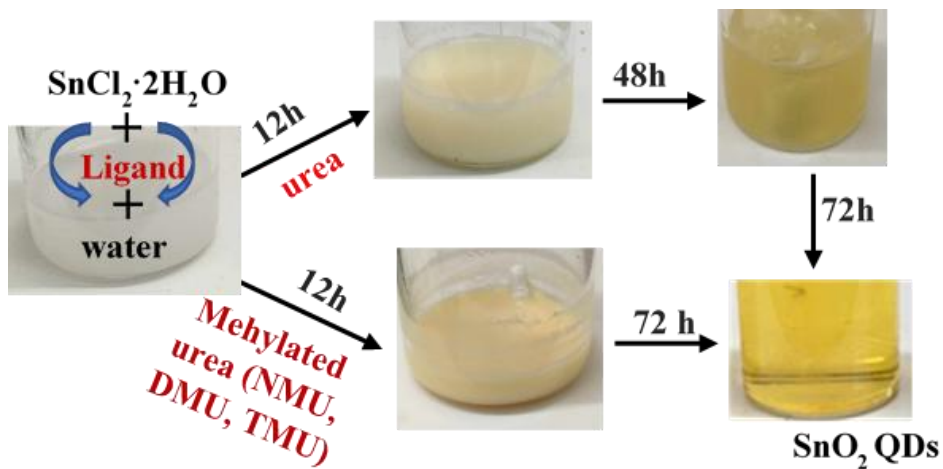
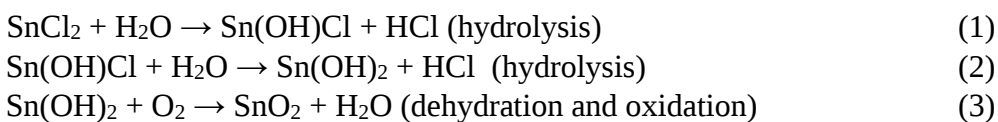


Figure S2. Synthetic pathway of urea and methylated urea-based SnO<sub>2</sub> QDs.

SnO<sub>2</sub> QDs formation processes (synthesis steps provided below).<sup>1</sup>



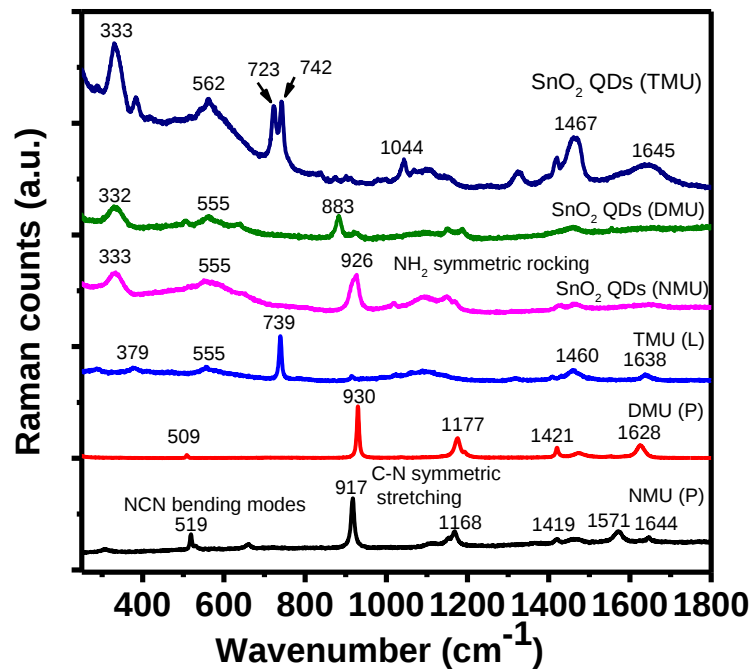


Figure S3. Raman spectra of urea-based ligands and corresponding SnO<sub>2</sub> QDs solutions.

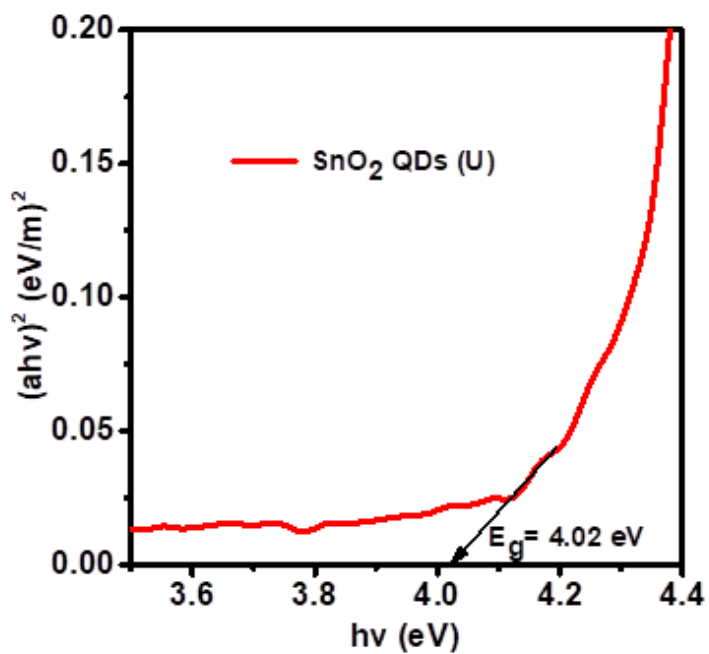


Figure S4. Calculated optical band gap of SnO<sub>2</sub> QD (U).

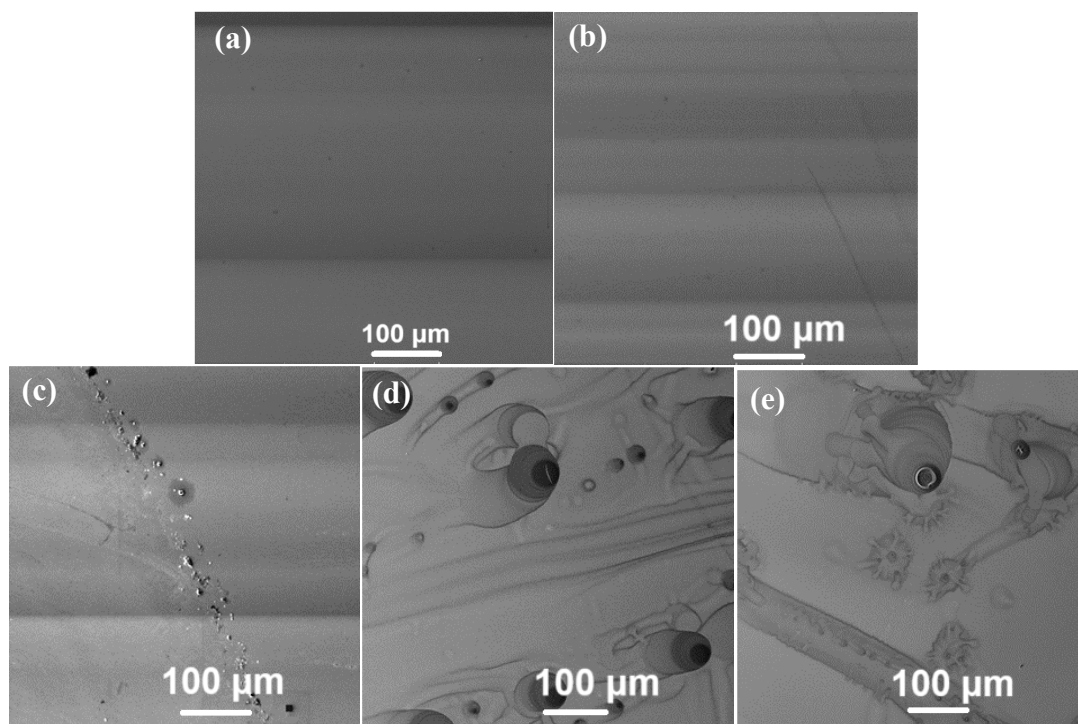


Figure S5. Top-view SEM images at low magnification for SnO<sub>2</sub> QDs derived from (a) thiourea, (b) urea, (c) NMU, (d) DMU, and (e) DMU deposited on FTO.

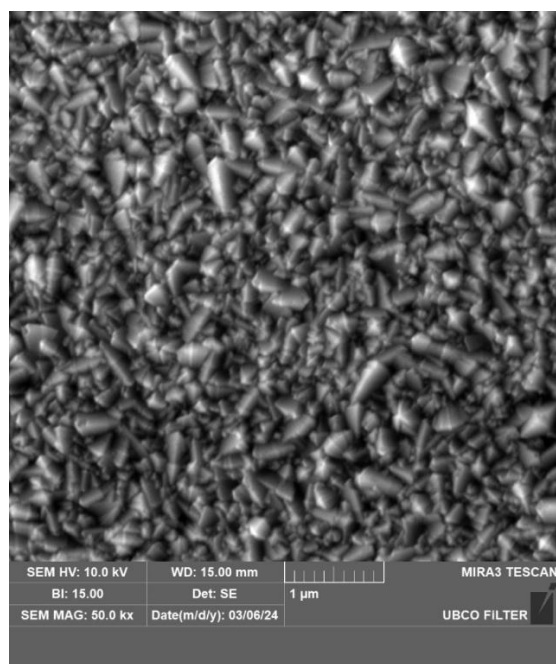


Figure S6. Top-view SEM image of bare FTO.

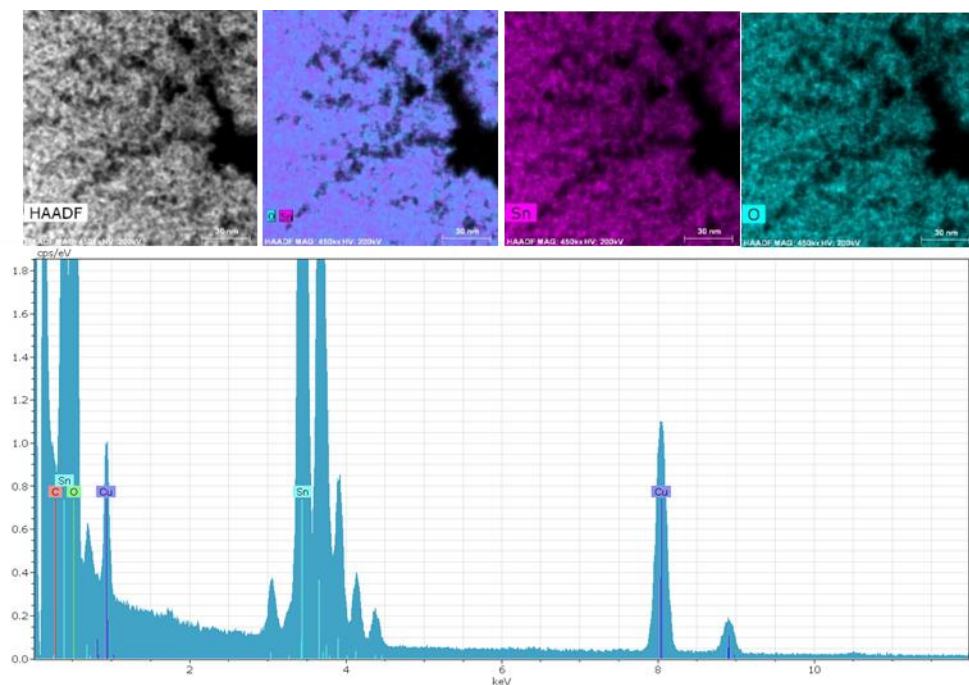


Figure S7. High-angle annular dark-field (HAADF) STEM image maps of  $\text{SnO}_2$  (U).

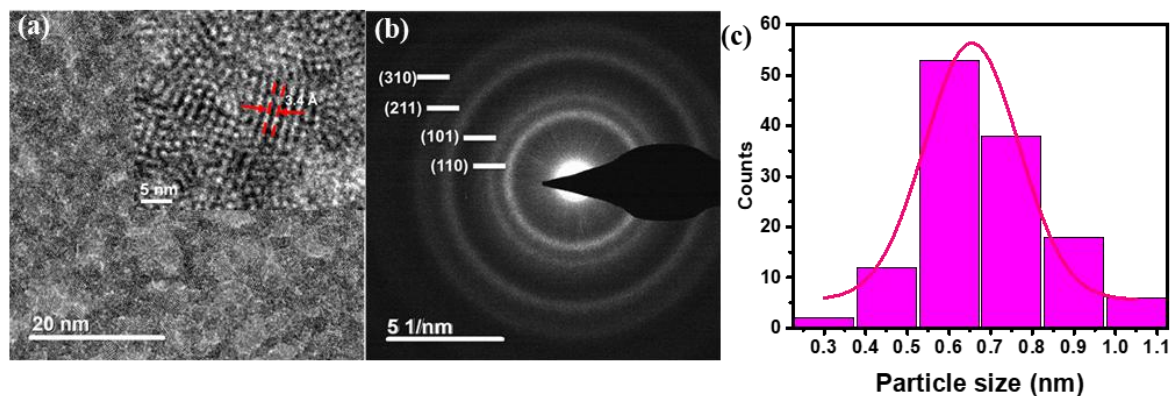


Figure S8. (a) Transmission electron microscopy (TEM) images of  $\text{SnO}_2$  QDs (NMU, methylated urea). (b) SAED pattern of  $\text{SnO}_2$  QD of  $\text{SnO}_2$  QDs (NMU), and (c) particle size distribution of  $\text{SnO}_2$  QDs (NMU).

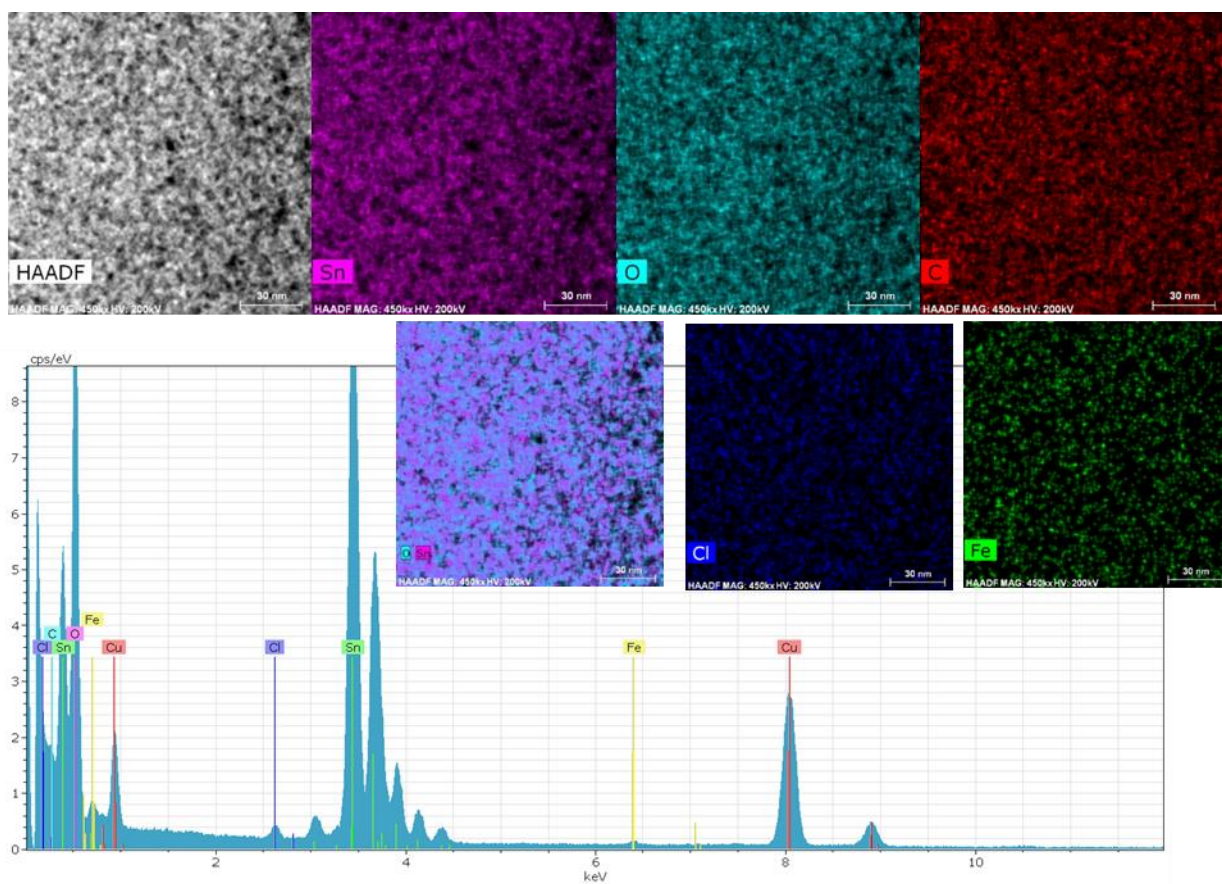


Figure S9. High-angle annular dark-field (HAADF) STEM image maps of SnO<sub>2</sub> (methylated urea (NMU)).

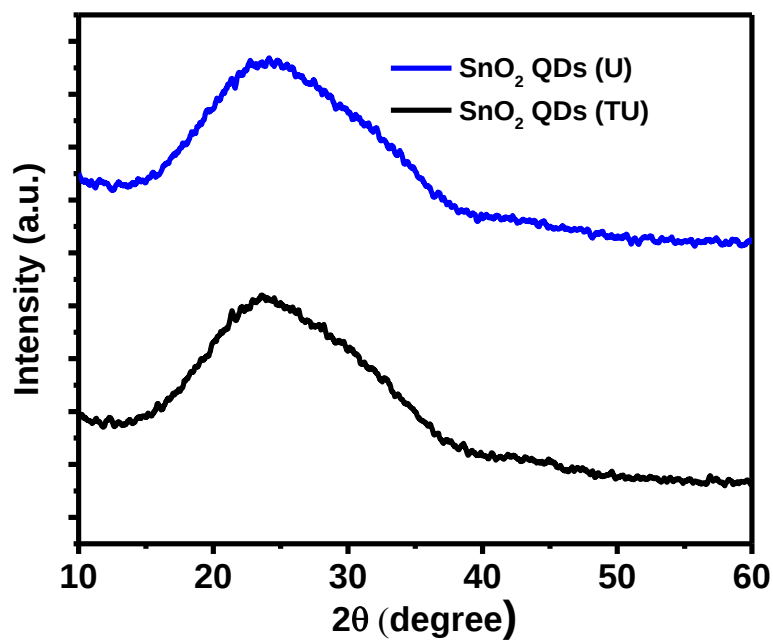


Figure S10. (a) XRD patterns of SnO<sub>2</sub> QDs on glass annealed at 150 °C.

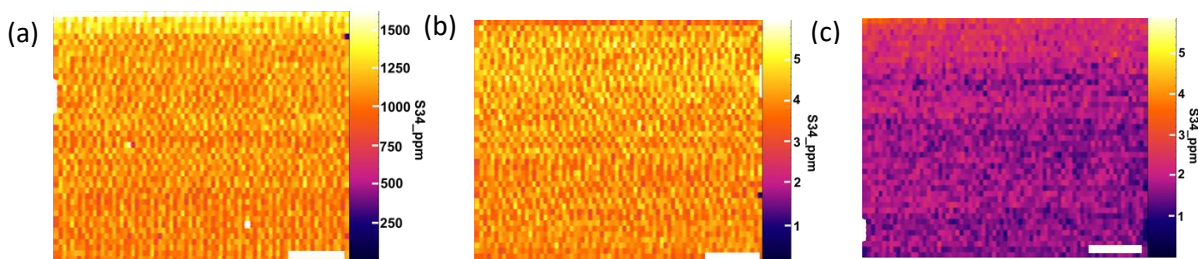


Figure S11. Laser ablation inductively-coupled plasma mass spectrometry (LA-ICP-MS) elemental distribution of S (34S) SnO<sub>2</sub> QDs synthesized from: (a) TU annealed at 150 °C, (b) TU annealed at 200 °C, and (c) U annealed at 150 °C (Scale bar : 200 μm).

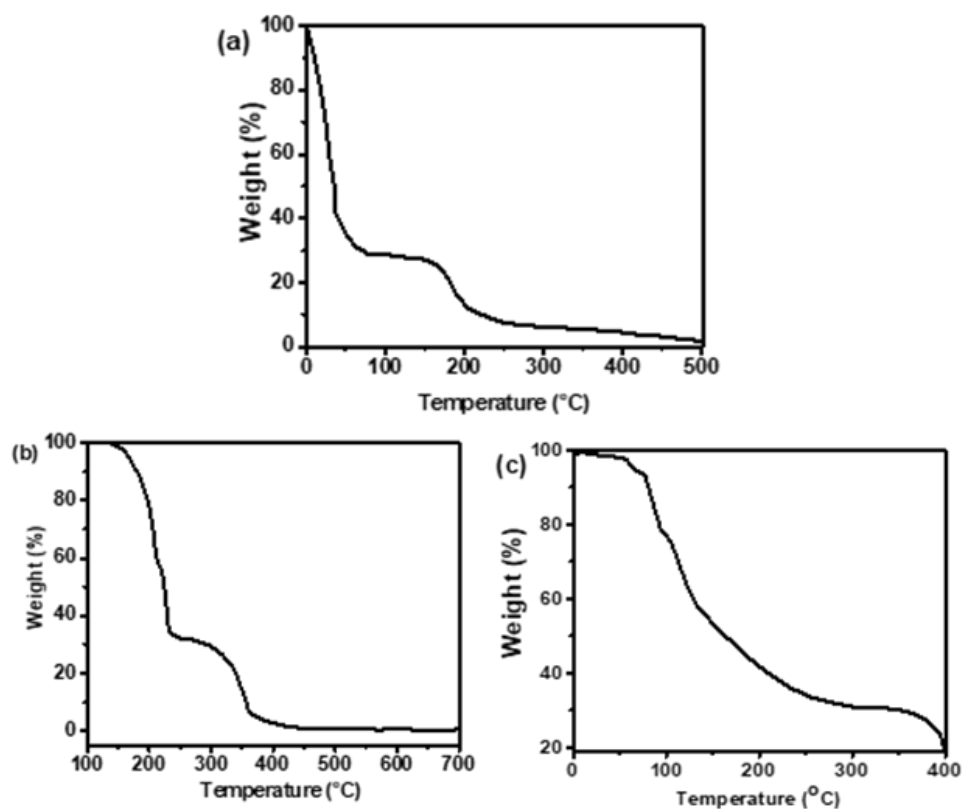


Figure S12. Thermogravimetric analysis (TGA) curves of: (a) thiourea, (b), urea, (c) methylated urea (TMU).<sup>2-4</sup>

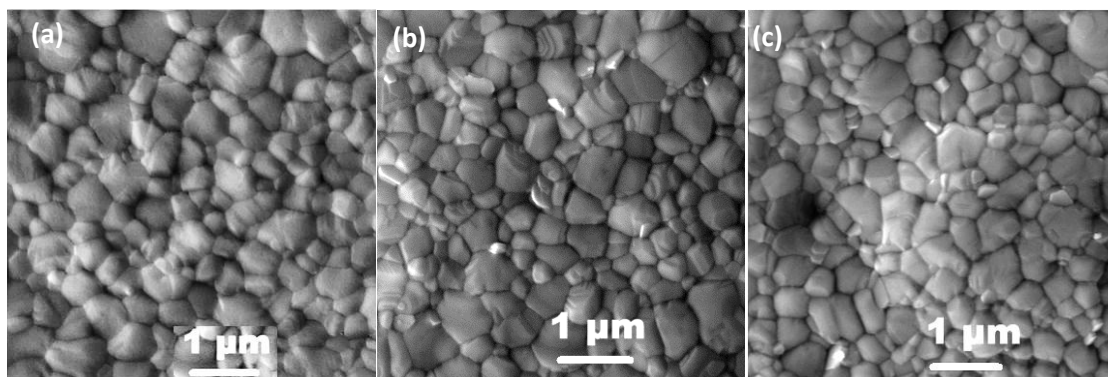


Figure S13. SEM image of  $\text{Cs}_{0.1}\text{FA}_{0.90}\text{PbI}_3$  on: (a)  $\text{SnO}_2$  QDs thin film (TU), (b)  $\text{SnO}_2$  QDs thin film (U), and (c)  $\text{SnO}_2$  QDs thin film (methylated, NMU).

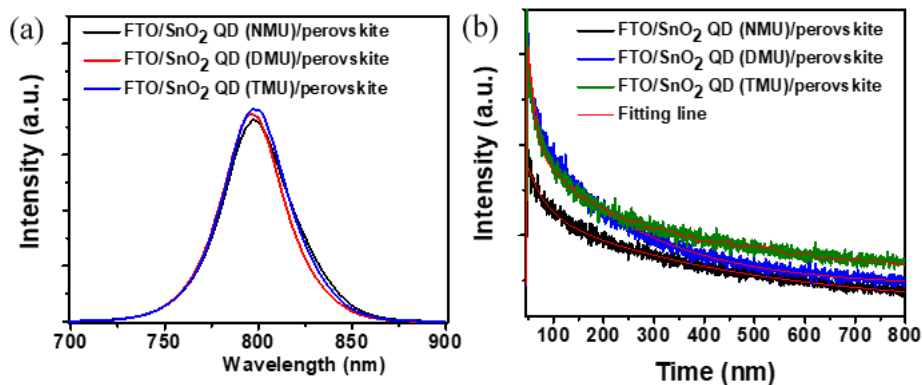


Figure S14. PL spectra of the FTO/SnO<sub>2</sub> QDs /perovskite, and (d) TRPL spectra of the FTO/SnO<sub>2</sub> QDs/perovskite (for the methylated urea-based SnO<sub>2</sub> QDs).

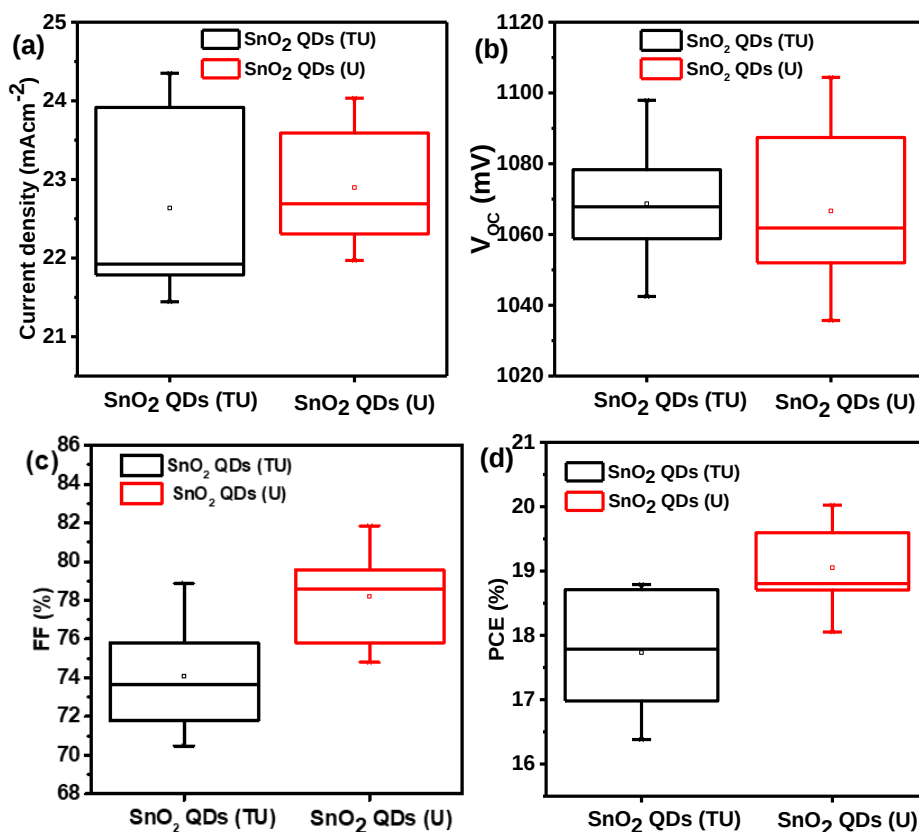


Figure S15. Statistical box plots of the PV parameters obtained from devices using various SnO<sub>2</sub> QDs as ETL: (a)  $J_{SC}$ , (b)  $V_{OC}$ , (c) FF, and (d) PCE. Boxes show the interquartile range (25th to 75th percentiles), the horizontal line inside boxes show the median, while whiskers show the lowest and highest values.

Table S1: Photovoltaic parameters of PSCs based on the urea-derived SnO<sub>2</sub> QDs ETLs at various annealing temperatures.

| Temperature<br>(°C) | J <sub>sc</sub><br>(mAcm <sup>-2</sup> ) | V <sub>oc</sub><br>(mV) | FF<br>(%)  | PCE<br>(%) |
|---------------------|------------------------------------------|-------------------------|------------|------------|
| 70                  | 20.95±0.58                               | 1027±25.9               | 74.65±2.89 | 16.06±0.44 |
| 100                 | 21.22±0.43                               | 1078±24.9               | 75.83±3.20 | 17.35±0.71 |
| 150                 | 22.72±0.70                               | 1079±18.9               | 78.42±1.92 | 19.23±0.49 |
| 200                 | 21.86±1.02                               | 1068±42.5               | 77.96±1.06 | 18.20±0.54 |

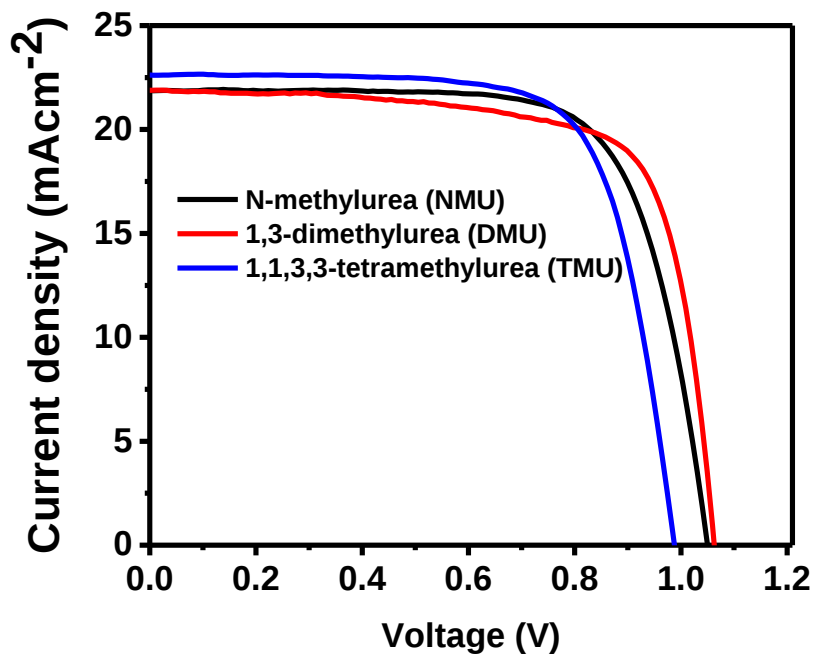


Figure S16. J–V curves of methylated urea-derived SnO<sub>2</sub> QDs-based PSCs.

Table S2: Photovoltaic parameters of PSCs based on SnO<sub>2</sub> QD ETLs (methylated urea, averaged over 10 devices).

| SnO <sub>2</sub> QDs  | J <sub>SC</sub> (mAcm <sup>-2</sup> ) | V <sub>OC</sub> (mV) | FF (%)     | PCE (%)    |
|-----------------------|---------------------------------------|----------------------|------------|------------|
| SnO <sub>2</sub> -NMU | 20.91±0.63                            | 1038±25.8            | 74.58±2.08 | 16.18±0.31 |
| SnO <sub>2</sub> -DMU | 20.84±0.72                            | 1037±25.8            | 74.53±2.88 | 16.11±0.32 |
| SnO <sub>2</sub> -TMU | 20.82±0.83                            | 1037±21.9            | 74.16±1.26 | 16.00±0.23 |

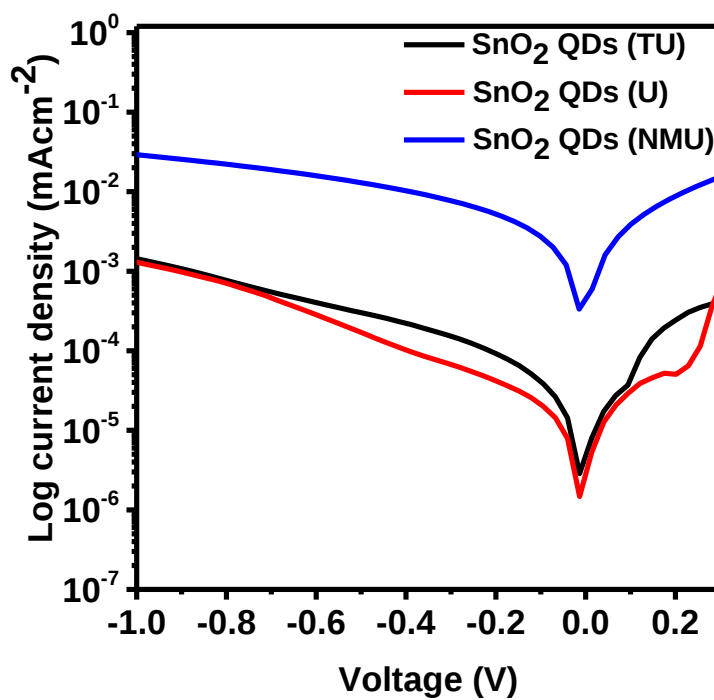


Figure S17. Dark current curves of SnO<sub>2</sub> QD-based PSCs.

Table S3: Photovoltaic comparison and synthetic methods of SnO<sub>2</sub> QDs as ETLs in PSCs (room temperature ink synthesis indicated with (r.t.))

| Device structure                                                                                                                                                                | Synthetic Method                                   | V <sub>oc</sub> (mV) | J <sub>sc</sub> (mAcm <sup>-2</sup> ) | FF (%) | PCE (%) | Active area (cm <sup>2</sup> ) | Ref. |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------|----------------------|---------------------------------------|--------|---------|--------------------------------|------|
| FTO/SnO <sub>2</sub> QDs/ SnO <sub>2</sub> NC/CsMAFAPbI <sub>3</sub> Br <sub>3-x</sub> /Spiro-OMeTAD/Ag                                                                         | 2-(2-aminoethyl) isothiourea dihydrobromide (r.t.) | 1.19                 | 24.75                                 | 78.20  | 23.00   | 0.04                           | [1]  |
| ITO/SnO <sub>2</sub> QDs / (Cs <sub>0.05</sub> (FA <sub>0.83</sub> MA <sub>0.17</sub> ) <sub>0.95</sub> Pb(I <sub>0.83</sub> Br <sub>0.17</sub> ) <sub>3</sub> spiro-OMeTAD/ Au | CH <sub>4</sub> N <sub>2</sub> S reaction (r.t.)   | 1.09                 | 19.50                                 | 78.00  | 16.60   | 0.1                            | [6]  |
| FTO/SnO <sub>2</sub> QDs / (FAPbI <sub>3</sub> ) <sub>0.875</sub> (CsPbBr <sub>3</sub> ) <sub>0.125</sub> /spiro-OMeTAD/ Au                                                     | CH <sub>4</sub> N <sub>2</sub> S reaction (r.t.)   | 1.10                 | 23.02                                 | 77.50  | 19.80   | 1.0                            | [7]  |
| FTO/TiO <sub>2</sub> /SnO <sub>2</sub> QDs/CsMAFAPbI <sub>3</sub> Br <sub>3-x</sub> /Spiro-OMeTAD/Au                                                                            | CH <sub>4</sub> N <sub>2</sub> S reaction (r.t.)   | 1.11                 | 20.70                                 | 75.30  | 17.31   | 0.09                           | [8]  |
| FTO/SnO <sub>2</sub> QDs/CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> /Spiro-OMeTAD/Ag                                                                                      | CH <sub>4</sub> N <sub>2</sub> S reaction (r.t.)   | 1.06                 | 21.60                                 | 74.61  | 17.01   | NA                             | [9]  |
| FTO/SnO <sub>2</sub> QDs/ SnO <sub>2</sub> NC/CsMAFAPbI <sub>3</sub> Br <sub>3-x</sub> /Spiro-OMeTAD/Ag                                                                         | CH <sub>4</sub> N <sub>2</sub> S reaction (r.t.)   | 1.08                 | 23.05                                 | 81.63  | 20.32   | 0.04                           | [10] |
| FTO/SnO <sub>2</sub> QDs/CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> /Spiro-OMeTAD/MoO <sub>x</sub> /Al                                                                    | solvothermal technique                             | 0.99                 | 18.80                                 | 69.00  | 12.90   | 0.1                            | [11] |
| ITO/SnO <sub>2</sub> /SnO <sub>2</sub> QDs/MAPbI <sub>3</sub> / carbon                                                                                                          | CTAB (r.t.)                                        | 0.85                 | 19.77                                 | 70.00  | 11.76   | NA                             | [12] |
| FTO/SnO <sub>2</sub> / QDs/MAPbI <sub>3</sub> /Spiro-OMeTAD/Ag                                                                                                                  | Microwave-assisted                                 | 1.14                 | 23.38                                 | 76.20  | 20.24   | NA                             | [13] |

|                                                                                                                              |                                                      |      |       |       |       |      |              |
|------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------|------|-------|-------|-------|------|--------------|
| FTO/SnO <sub>2</sub> / QDs/<br>MAPbI <sub>3</sub> ) <sub>0.7</sub> (FAPbI <sub>3</sub> ) <sub>0.3</sub> /S<br>piro-OMeTAD/Au | solution<br>processing                               | 1.08 | 23.40 | 74.00 | 18.80 | 0.09 | [14]         |
| FTO/SnO <sub>2</sub> QDs/<br>CS <sub>0.1</sub> FA <sub>0.9</sub> PbI <sub>3</sub> /Spiro-<br>OMeTAD/Ag                       | CO(NH <sub>2</sub> ) <sub>2</sub><br>reaction (r.t.) | 1.04 | 23.60 | 81.85 | 20.01 | 0.16 | This<br>work |

## REFERENCES

- (1) Ren, Z.; Liu, K.; Hu, H.; Guo, X.; Gao, Y.; Fong, P. W. K.; Liang, Q.; Tang, H.; Huang, J.; Zhang, H.; et al. Room-Temperature Multiple Ligands-Tailored SnO<sub>2</sub> Quantum Dots Endow in Situ Dual-Interface Binding for Upscaling Efficient Perovskite Photovoltaics with High V<sub>OC</sub>. *Light Sci. Appl.* **2021**, *10*, 239.
- (2) Ogawa, H.; Sato, Y.; Mori, H. Tetramethylurea Dimer/Lithium Salt-Based Deep Eutectics as a Novel Class of Eutectic Electrolytes. *Mater. Chem. Front.* **2021**, *5*, 8078–8085.
- (3) Zhang, H.; Xi, Y.; Su, C.; Liu, Z. G. Lab Study of Urea Deposit Formation and Chemical Transformation Process of Diesel Aftertreatment System. In *SAE Technical Papers*; SAE International, **2017**, 2017-01-0915.
- (4) Park, S. N.; Sung, S. J.; Son, D. H.; Kim, D. H.; Gansukh, M.; Cheong, H.; Kang, J. K. Solution-Processed Cu<sub>2</sub>ZnSnS<sub>4</sub> Absorbers Prepared by Appropriate Inclusion and Removal of Thiourea for Thin Film Solar Cells. *RSC Adv.* **2014**, *4*, 9118–9125.
- (6) Sannino, G. V.; Gries, T. W.; Wang, Q.; Caso, M. F.; De Maria, A.; Lancellotti, L.; Mercaldo, L. V.; Muñoz-García, A. B.; Pavone, M.; Abate, A.; Delli Veneri, P. Optimizing SnO<sub>2</sub> Quantum Dot Precursor Solutions for Perovskite Solar Cells with Reduced Hysteresis. *Solar RRL* **2024**, *8*,
- (7) Yang, G.; Chen, C.; Yao, F.; Chen, Z.; Zhang, Q.; Zheng, X.; Ma, J.; Lei, H.; Qin, P.; Xiong, L.; et al. Effective Carrier-Concentration Tuning of SnO<sub>2</sub> Quantum Dot Electron-Selective Layers for High-Performance Planar Perovskite Solar Cells. *Advanced Materials* **2018**, *30*, 1706023.
- (8) Wu, T.; Zhen, C.; Wu, J.; Jia, C.; Haider, M.; Wang, L.; Liu, G.; Cheng, H. M. Chlorine Capped SnO<sub>2</sub> Quantum-Dots Modified TiO<sub>2</sub> Electron Selective Layer to Enhance the Performance of Planar Perovskite Solar Cells. *Sci. Bull. (Beijing)*. **2019**, *64*, 547–552.
- (9) Wang, E.; Chen, P.; Yin, X.; Wu, Y.; Que, W. Tailoring Electronic Properties of SnO<sub>2</sub> Quantum Dots via Aluminum Addition for High-Efficiency Perovskite Solar Cells. *Solar RRL* **2019**, *3*, 1900041.

- (10) Luo, Z.; Du, G.; Yang, L.; Zhang, J. Unveiling the Dimensional Effects of SnO<sub>2</sub> Quantum Dots and Nanoparticles on the Interfacial Properties of Perovskite Solar Cells. *J. Power Sources* **2023**, *568*, 232928.
- (11) Kiani, M. S.; Parkhomenko, H. P.; Mangrulkar, M.; Aigarayeva, S.; Akhanuly, A.; Shalenov, E. O.; Ng, A.; Jumabekov, A. N. Stepping toward Portable Optoelectronics with SnO<sub>2</sub> Quantum Dot-Based Electron Transport Layers. *ACS Omega* **2023**, *8*, 21212–21222.
- (12) Youssef, R. M.; Salem, A. M. S.; Shawky, A.; Ebrahim, S.; Soliman, M.; Abdel-Mottaleb, M. S. A.; El-Sheikh, S. M. Solution-Processed Quantum Dot SnO<sub>2</sub> as an Interfacial Electron Transporter for Stable Fully-Air-Fabricated Metal-Free Perovskite Solar Cells. *Journal of Materiomics* **2022**, *8*, 1172–1183.
- (13) Xu, Z.; Jiang, Y.; Li, Z.; Chen, C.; Kong, X.; Chen, Y.; Zhou, G.; Liu, J. M.; Kempa, K.; Gao, J. Rapid Microwave-Assisted Synthesis of SnO<sub>2</sub> Quantum Dots for Efficient Planar Perovskite Solar Cells. *ACS Appl. Energy Mater.* **2021**, *4*, 1887–1893.
- (14) Liu, H.; Chen, Z.; Wang, H.; Ye, F.; Ma, J.; Zheng, X.; Gui, P.; Xiong, L.; Wen, J.; Fang, G. A Facile Room Temperature Solution Synthesis of SnO<sub>2</sub> Quantum Dots for Perovskite Solar Cells. *J. Mater. Chem. A Mater.* **2019**, *7*, 10636–10643.